

# Rositsa T Yakimova

## List of Publications by Year in descending order

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170  
papers

4,432  
citations

126708

33  
h-index

138251

58  
g-index

171  
all docs

171  
docs citations

171  
times ranked

5163  
citing authors

#	ARTICLE	IF	CITATIONS
1	Homogeneous large-area graphene layer growth on $\text{SiC}(0001)$ . Physical Review B, 2008, 78, .	1.1	539
2	Epitaxially grown graphene based gas sensors for ultra sensitive NO <sub>2</sub> detection. Sensors and Actuators B: Chemical, 2011, 155, 451-455.	4.0	297
3	Epitaxial Graphene on SiC: A Review of Growth and Characterization. Crystals, 2016, 6, 53.	1.0	169
4	Si intercalation/deintercalation of graphene on $\text{SiC}(0001)$ . Physical Review B, 2012, 85, .	1.1	115
5	High temperature chemical vapor deposition of SiC. Applied Physics Letters, 1996, 69, 1456-1458.	1.5	111
6	Anomalously strong pinning of the filling factor $\nu = 1/2$ in epitaxial graphene. Physical Review B, 2011, 83, .	1.1	110
7	On the interaction of toxic Heavy Metals (Cd, Hg, Pb) with graphene quantum dots and infinite graphene. Scientific Reports, 2017, 7, 3934.	1.6	94
8	Continuous sensing of hydrogen peroxide and glucose via quenching of the UV and visible luminescence of ZnO nanoparticles. Mikrochimica Acta, 2015, 182, 1819-1826.	2.5	82
9	A 3 kV Schottky barrier diode in 4H-SiC. Applied Physics Letters, 1998, 72, 445-447.	1.5	72
10	Growth of 6H and 4H-SiC by sublimation epitaxy. Journal of Crystal Growth, 1999, 197, 155-162.	0.7	71
11	Novel material concepts of transducers for chemical and biosensors. Biosensors and Bioelectronics, 2007, 22, 2780-2785.	5.3	66
12	Operation of graphene quantum Hall resistance standard in a cryogen-free table-top system. 2D Materials, 2015, 2, 035015.	2.0	63
13	Uniform doping of graphene close to the Dirac point by polymer-assisted assembly of molecular dopants. Nature Communications, 2018, 9, 3956.	5.8	61
14	ZnO films formed by atomic layer deposition as an optical biosensor platform for the detection of Grapevine virus A-type proteins. Biosensors and Bioelectronics, 2017, 92, 763-769.	5.3	60
15	Stacking of adjacent graphene layers grown on C-face SiC. Physical Review B, 2011, 84, .	1.1	53
16	A nanostructured NiO/cubic SiC $\text{n}^{\text{th}}$ heterojunction photoanode for enhanced solar water splitting. Journal of Materials Chemistry A, 2019, 7, 4721-4728.	5.2	50
17	Organosilane-functionalized wide band gap semiconductor surfaces. Applied Physics Letters, 2007, 90, 223904.	1.5	48
18	Layer-number determination in graphene on SiC by reflectance mapping. Carbon, 2014, 77, 492-500.	5.4	48

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19	Non-contact method for measurement of the microwave conductivity of graphene. Applied Physics Letters, 2013, 103, .	1.5	47
20	Small epitaxial graphene devices for magnetosensing applications. Journal of Applied Physics, 2012, 111, 07E509.	1.1	46
21	Lateral Enlargement Growth Mechanism of 3C-SiC on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2014, 14, 6514-6520.	1.4	46
22	Detection of Ultralow Concentration NO <sub>2</sub> in Complex Environment Using Epitaxial Graphene Sensors. ACS Sensors, 2018, 3, 1666-1674.	4.0	45
23	Indium Nitride at the 2D Limit. Advanced Materials, 2021, 33, e2006660.	11.1	45
24	Energy loss rates of hot Dirac fermions in epitaxial, exfoliated, and CVD graphene. Physical Review B, 2013, 87, .	1.1	44
25	Structural improvement in sublimation epitaxy of 4H-SiC. Journal of Applied Physics, 2000, 88, 1407-1411.	1.1	42
26	Fast growth of high quality GaN. Physica Status Solidi A, 2003, 200, 13-17.	1.7	42
27	Aligned AlN nanowires by self-organized vapor-solid growth. Nanotechnology, 2009, 20, 495304.	1.3	41
28	Effect of impurity incorporation on crystallization in AlN sublimation epitaxy. Journal of Applied Physics, 2004, 96, 5293-5297.	1.1	40
29	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2015, 15, 2940-2947.	1.4	38
30	Combining graphene with silicon carbide: synthesis and properties – a review. Semiconductor Science and Technology, 2016, 31, 113004.	1.0	38
31	Graphene integration with nitride semiconductors for high power and high frequency electronics. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600460.	0.8	38
32	Phase Space for the Breakdown of the Quantum Hall Effect in Epitaxial Graphene. Physical Review Letters, 2013, 111, 096601.	2.9	37
33	Improved Ni ohmic contact on n-type 4H-SiC. Journal of Electronic Materials, 1997, 26, 119-122.	1.0	34
34	Contribution of free-electron recombination to the luminescence spectra of thick GaN films grown by hydride vapor phase epitaxy. Journal of Applied Physics, 1999, 85, 7888-7892.	1.1	34
35	Real-time sensing of lead with epitaxial graphene-integrated microfluidic devices. Sensors and Actuators B: Chemical, 2019, 288, 425-431.	4.0	34
36	Nanoporous Cubic Silicon Carbide Photoanodes for Enhanced Solar Water Splitting. ACS Nano, 2021, 15, 5502-5512.	7.3	34

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37	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , 2021, 14, 5348.	1.3	34
38	Visible to vacuum ultraviolet dielectric functions of epitaxial graphene on 3C and 4H SiC polytypes determined by spectroscopic ellipsometry. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	33
39	Barrier height determination for n-type 4H-SiC schottky contacts made using various metals. <i>Journal of Electronic Materials</i> , 1998, 27, 871-875.	1.0	32
40	Narrow photoemission lines from graphite valence states. <i>Physical Review B</i> , 2002, 66, .	1.1	32
41	Giant quantum Hall plateaus generated by charge transfer in epitaxial graphene. <i>Scientific Reports</i> , 2016, 6, 30296.	1.6	32
42	Atomic-Scale Tuning of Graphene/Cubic SiC Schottky Junction for Stable Low-Bias Photoelectrochemical Solar-to-Fuel Conversion. <i>ACS Nano</i> , 2020, 14, 4905-4915.	7.3	31
43	New Materials for Chemical and Biosensors. <i>Materials and Manufacturing Processes</i> , 2006, 21, 253-256.	2.7	30
44	Properties and potential applications of two-dimensional AlN. <i>Vacuum</i> , 2020, 176, 109231.	1.6	30
45	Effect of initial substrate conditions on growth of cubic silicon carbide. <i>Journal of Crystal Growth</i> , 2011, 324, 7-14.	0.7	29
46	Considerably long carrier lifetimes in high-quality 3C-SiC(111). <i>Applied Physics Letters</i> , 2012, 100, .	1.5	29
47	Microstructure and luminescence dynamics of ZnCdO films with high Cd content deposited on different substrates by DC magnetron sputtering method. <i>Applied Surface Science</i> , 2013, 276, 550-557.	3.1	29
48	Charge neutrality in epitaxial graphene on $\sqrt{3}\times\sqrt{3}$ R120° SiC(111) via nitrogen intercalation. <i>Physical Review B</i> , 2015, 92, .	1.1	29
49	Insights into the origin of the excited transitions in graphene quantum dots interacting with heavy metals in different media. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 30445-30463.	1.3	29
50	Role of the Potential Barrier in the Electrical Performance of the Graphene/SiC Interface. <i>Crystals</i> , 2017, 7, 162.	1.0	29
51	Large-area microfocal spectroscopic ellipsometry mapping of thickness and electronic properties of epitaxial graphene on Si- and C-face of 3C-SiC(111). <i>Applied Physics Letters</i> , 2013, 102, .	1.5	28
52	Application of ZnO Nanorods Based Whispering Gallery Mode Resonator in Optical Immunosensors. <i>Colloids and Surfaces B: Biointerfaces</i> , 2020, 191, 110999.	2.5	28
53	Cathodoluminescence identification of donor-acceptor related emissions in as-grown 4H-SiC layers. <i>Journal of Applied Physics</i> , 2002, 91, 2890-2895.	1.1	27
54	Monolayer graphene/SiC Schottky barrier diodes with improved barrier height uniformity as a sensing platform for the detection of heavy metals. <i>Beilstein Journal of Nanotechnology</i> , 2016, 7, 1800-1814.	1.5	27

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55	Investigation of ZnO as a perspective material for photonics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 144-149.	0.8	25
56	A prototype of RK/200 quantum Hall array resistance standard on epitaxial graphene. <i>Journal of Applied Physics</i> , 2015, 118, 044506.	1.1	25
57	Performance tuning of gas sensors based on epitaxial graphene on silicon carbide. <i>Materials and Design</i> , 2018, 153, 153-158.	3.3	25
58	Towards quantum-limited coherent detection of terahertz waves in charge-neutral graphene. <i>Nature Astronomy</i> , 2019, 3, 983-988.	4.2	25
59	Epitaxial Graphene Sensors Combined with 3D-Printed Microfluidic Chip for Heavy Metals Detection. <i>Sensors</i> , 2019, 19, 2393.	2.1	24
60	Seed-Layer-Free Atomic Layer Deposition of Highly Uniform Al <sub>2</sub> O <sub>3</sub> Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. <i>Advanced Materials Interfaces</i> , 2019, 6, 1900097.	1.9	24
61	Electrical behavior of 4H-SiC metal-oxide-semiconductor structures with Al <sub>2</sub> O <sub>3</sub> as gate dielectric. <i>Journal of Applied Physics</i> , 2005, 97, 124507.	1.1	23
62	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , 2017, 116, 722-732.	5.4	23
63	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. <i>Scientific Reports</i> , 2017, 7, 5151.	1.6	23
64	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. <i>Nanotechnology</i> , 2019, 30, 284003.	1.3	23
65	Interband transitions in closed-shell vacancy containing graphene quantum dots complexed with heavy metals. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 21528-21543.	1.3	22
66	Graphene Decorated with Iron Oxide Nanoparticles for Highly Sensitive Interaction with Volatile Organic Compounds. <i>Sensors</i> , 2019, 19, 918.	2.1	22
67	Aluminum oxide nucleation in the early stages of atomic layer deposition on epitaxial graphene. <i>Carbon</i> , 2020, 169, 172-181.	5.4	22
68	Dislocation loop evolution in ion implanted 4H-SiC. <i>Journal of Applied Physics</i> , 2003, 93, 9395-9397.	1.1	20
69	Interface disorder probed at the atomic scale for graphene grown on the C face of SiC. <i>Physical Review B</i> , 2015, 91, .	1.1	20
70	Metal-dielectric transition in Sn-intercalated graphene on SiC(0001). <i>Ultramicroscopy</i> , 2017, 183, 49-54.	0.8	20
71	Flat-Band Electronic Structure and Interlayer Spacing Influence in Rhombohedral Four-Layer Graphene. <i>Nano Letters</i> , 2018, 18, 5862-5866.	4.5	20
72	Graphene-Based Ammonia Sensors Functionalised with Sub-Monolayer V <sub>2</sub> O <sub>5</sub> : A Comparative Study of Chemical Vapour Deposited and Epitaxial Graphene. <i>Sensors</i> , 2019, 19, 951.	2.1	20

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73	Exploring NiO nanosize structures for ammonia sensing. Journal of Materials Science: Materials in Electronics, 2018, 29, 11870-11877.	1.1	19
74	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	1.1	18
75	Puddle-Induced Resistance Oscillations in the Breakdown of the Graphene Quantum Hall Effect. Physical Review Letters, 2016, 117, 237702.	2.9	18
76	Monitoring of epitaxial graphene anodization. Electrochimica Acta, 2017, 238, 91-98.	2.6	18
77	Lead (Pb) interfacing with epitaxial graphene. Physical Chemistry Chemical Physics, 2018, 20, 17105-17116.	1.3	18
78	Atomically manipulated proton transfer energizes water oxidation on silicon carbide photoanodes. Journal of Materials Chemistry A, 2018, 6, 24358-24366.	5.2	17
79	Polymer-encapsulated molecular doped epigraphene for quantum resistance metrology. Metrologia, 2019, 56, 045004.	0.6	17
80	Effect of epitaxial graphene morphology on adsorption of ambient species. Applied Surface Science, 2019, 486, 239-248.	3.1	17
81	Ultraviolet Detectors Based on ZnO:N Thin Films with Different Contact Structures. Acta Physica Polonica A, 2008, 114, 1123-1129.	0.2	17
82	Changes in work function due to $\text{NO}_2$ adsorption on monolayer and bilayer epitaxial graphene on SiC(0001). Physical Review B, 2016, 94, .	1.1	16
83	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. Materials Science in Semiconductor Processing, 2019, 96, 145-152.	1.9	16
84	Cubic SiC Photoanode Coupling with Ni:FeOOH Oxygen $\text{H}_2\text{O}$ Evolution Cocatalyst for Sustainable Photoelectrochemical Water Oxidation. Solar Rrl, 2020, 4, 1900364.	3.1	16
85	High mobility epitaxial graphene devices via aqueous-ozone processing. Applied Physics Letters, 2015, 106, 063503.	1.5	15
86	Atomic Layer Deposition of High-k Insulators on Epitaxial Graphene: A Review. Applied Sciences (Switzerland), 2020, 10, 2440.	1.3	15
87	A study of thick 3C-SiC epitaxial layers grown on 6H-SiC substrates by sublimation epitaxy in vacuum. Semiconductors, 2007, 41, 263-265.	0.2	14
88	Origin of the $\Gamma$ -band replicas in the electronic structure of graphene grown on $\text{SiC}(0001)$ . Physical Review B, 2019, 99, .	1.1	14
89	Electrochemical Deposition of Copper on Epitaxial Graphene. Applied Sciences (Switzerland), 2020, 10, 1405.	1.3	14
90	Interfacial reactions and ohmic contact formation in the Ni/Al $\text{SiC}$ system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3252.	1.6	13

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91	Aligned AlN nanowires and microrods by self-patterning. <i>Applied Physics Letters</i> , 2007, 90, 123103.	1.5	13
92	Formation of needle-like and columnar structures of AlN. <i>Journal of Crystal Growth</i> , 2007, 300, 130-135.	0.7	13
93	Interaction of epitaxial graphene with heavy metals: towards novel sensing platform. <i>Nanotechnology</i> , 2019, 30, 294002.	1.3	13
94	Interband Absorption in Few-Layer Graphene Quantum Dots: Effect of Heavy Metals. <i>Materials</i> , 2018, 11, 1217.	1.3	12
95	Study of annealing influence on electrical and morphological properties of ZnO:Ga thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 780-784.	0.8	11
96	Freestanding AlN single crystals enabled by self-organization of 2H-SiC pyramids on 4H-SiC substrates. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	11
97	Phase coherence and energy relaxation in epitaxial graphene under microwave radiation. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	11
98	Physics of a disordered Dirac point in epitaxial graphene from temperature-dependent magnetotransport measurements. <i>Physical Review B</i> , 2015, 92, .	1.1	11
99	Understanding Graphene Response to Neutral and Charged Lead Species: Theory and Experiment. <i>Materials</i> , 2018, 11, 2059.	1.3	11
100	Epitaxial Graphene on 4H-SiC (0001) as a Versatile Platform for Materials Growth: Mini-Review. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 5784.	1.3	11
101	Decoupling and ordering of multilayer graphene on C-face 3C-SiC(111). <i>Applied Physics Letters</i> , 2016, 109, .	1.5	10
102	Probing the uniformity of silver-doped epitaxial graphene by micro-Raman mapping. <i>Physica B: Condensed Matter</i> , 2020, 580, 411751.	1.3	10
103	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. <i>ACS Applied Nano Materials</i> , 2021, 4, 1282-1293.	2.4	10
104	Detection of strongly and weakly ionizing radiation by triode structure based on SiC films. <i>Journal of Applied Physics</i> , 2003, 93, 5714-5719.	1.1	9
105	Ambipolar charge transport in quasi-free-standing monolayer graphene on SiC obtained by gold intercalation. <i>Physical Review B</i> , 2020, 102, .	1.1	9
106	Exploring the Interface Landscape of Noble Metals on Epitaxial Graphene. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000673.	0.8	9
107	Computational Appraisal of Silver Nanocluster Evolution on Epitaxial Graphene: Implications for CO Sensing. <i>ACS Omega</i> , 2021, 6, 24739-24751.	1.6	9
108	Interaction of H and Li with epitaxial graphene on SiC: A comparative analysis by first principles study. <i>Applied Surface Science</i> , 2021, 568, 150988.	3.1	9

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109	Site-occupying behavior of boron in compensated p-type 4H-SiC grown by sublimation epitaxy. Journal of Applied Physics, 2002, 91, 3471-3473.	1.1	8
110	Silicon carbide grown by liquid phase epitaxy in microgravity. Journal of Materials Research, 1998, 13, 1812-1815.	1.2	7
111	Amplification of the signal in triode structures of ion detectors based on 6H-SiC epitaxial films. Applied Physics Letters, 2001, 79, 4447-4449.	1.5	7
112	Nanoscale 3-D $(E, k_x, k_y)$ band structure imaging on graphene and intercalated graphene. IBM Journal of Research and Development, 2011, 55, 6:1-6:6.	3.2	7
113	Structural Modifications in Epitaxial Graphene on SiC Following 10 keV Nitrogen Ion Implantation. Applied Sciences (Switzerland), 2020, 10, 4013.	1.3	7
114	Sublimation epitaxy of AlN layers on 4H-SiC depending on the type of crucible. Journal of Materials Science: Materials in Electronics, 2003, 14, 767-768.	1.1	6
115	Low-pressure sublimation epitaxy of AlN films—growth and characterization. Vacuum, 2004, 76, 143-146.	1.6	6
116	Properties of AlN epitaxial layers on 6H-SiC substrate grown by sublimation in argon, nitrogen, and their mixtures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 129, 228-231.	1.7	6
117	Structural characterization of ZnO nanopillars grown by atmospheric-pressure metalorganic chemical vapor deposition on vicinal 4H-SiC and SiO <sub>2</sub> /Si substrates. Journal of Applied Physics, 2011, 109, 043507-043507-8.	1.1	6
118	Shockley-Frank stacking faults in 6H-SiC. Journal of Applied Physics, 2012, 111, 113527.	1.1	6
119	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	2.2	6
120	Effect of boron on the resistivity of compensated 4H-SiC. Journal of Electronic Materials, 2003, 32, 452-457.	1.0	5
121	Surface Engineering of Functional Materials for Biosensors. , 0, , .		5
122	Fabrication of free-standing AlN crystals by controlled microrod growth. Journal of Crystal Growth, 2008, 310, 935-939.	0.7	5
123	Magnetic field driven ambipolar quantum Hall effect in epitaxial graphene close to the charge neutrality point. Physical Review B, 2017, 96, .	1.1	5
124	Chemical Sensing with Atomically Thin Platinum Templated by a 2D Insulator. Advanced Materials Interfaces, 2020, 7, 1902104.	1.9	5
125	The performance limits of epigraphene Hall sensors doped across the Dirac point. Applied Physics Letters, 2020, 116, .	1.5	5
126	Microhardness of 6H-SiC Epitaxial Layers Grown by Sublimation. Crystal Research and Technology, 1999, 34, 943-947.	0.6	4



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127	Polytype Stability and Defect Reduction in 4H-SiC Crystals Grown via Sublimation Technique. Materials Research Society Symposia Proceedings, 1999, 572, 265.	0.1	4
128	Highly Sensitive NH <sub>3</sub> Sensors Using CVD and Epitaxial Graphene Functionalised with Vanadium(V) Oxide: A Comparative Study. Proceedings (mdpi), 2018, 2, 854.	0.2	4
129	Large nonlocality in macroscopic Hall bars made of epitaxial graphene. Physical Review B, 2018, 98, .	1.1	4
130	Origin of layer decoupling in ordered multilayer graphene grown by high-temperature sublimation on C-face 4H-SiC. APL Materials, 2020, 8, .	2.2	4
131	Temperature-Dependent Photoluminescence of ZnO Thin Films Grown on Off-Axis SiC Substrates by APMOCVD. Materials, 2021, 14, 1035.	1.3	4
132	Special Issue "Fundamentals and Recent Advances in Epitaxial Graphene on SiC" Applied Sciences (Switzerland), 2021, 11, 3381.	1.3	4
133	Bidirectional Hydrogen Electrocatalysis on Epitaxial Graphene. ACS Omega, 2022, 7, 13221-13227.	1.6	4
134	Investigation of Structural Defects in 4H SiC Wafers. Materials Research Society Symposia Proceedings, 1994, 339, 729.	0.1	3
135	Synthesis of graphene oxide inks for printed electronics. , 2017, , .		3
136	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. Applied Sciences (Switzerland), 2021, 11, 1891.	1.3	3
137	Understanding of the Electrochemical Behavior of Lithium at Bilayer-Patched Epitaxial Graphene/4H-SiC. Nanomaterials, 2022, 12, 2229.	1.9	3
138	Domain Structure of Thick GaN Layers Grown by Hydride Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
139	Free-standing HVPE-GaN Layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1985-1988.	0.8	2
140	Microscopic lateral overgrowth by physical vapour transport of GaN on self-organized diamond-like carbon masks. Crystal Research and Technology, 2009, 44, 1078-1082.	0.6	2
141	Thermal Stability of Epitaxial Graphene Electrodes for Conductive Polymer Nanofiber Devices. Crystals, 2017, 7, 378.	1.0	2
142	Epitaxial Graphene Sensors Combined with 3D Printed Microfluidic Chip for Heavy Metals Detection. Proceedings (mdpi), 2018, 2, .	0.2	2
143	Bioelectrocatalysis on Anodized Epitaxial Graphene and Conventional Graphitic Interfaces. ChemElectroChem, 2019, 6, 3791-3796.	1.7	2
144	Manipulation of epitaxial graphene towards novel properties and applications. Materials Today: Proceedings, 2020, 20, 37-45.	0.9	2

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145	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. Applied Physics Letters, 2021, 119, 153902.	1.5	2
146	Strong field hole transport in 6H-SiC. Applied Physics Letters, 2009, 94, 082101.	1.5	1
147	Towards optimisation of epitaxially grown graphene based sensors for highly sensitive gas detection. , 2010, , .		1
148	Photon helicity driven currents in graphene. , 2010, , .		1
149	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Transactions, 2017, 80, 107-115.	0.3	1
150	Iron Oxide Nanoparticle Decorated Graphene for Ultra-Sensitive Detection of Volatile Organic Compounds. Proceedings (mdpi), 2018, 2, .	0.2	1
151	Structural and optical modification in 4H-SiC following 30 keV silver ion irradiation. AIP Conference Proceedings, 2018, , .	0.3	1
152	Epitaxial Graphene Growth on the Step-Structured Surface of Off-Axis C-Face 3C-SiC (1 $\bar{1}\bar{1}$ ). Physica Status Solidi (B): Basic Research, 2020, 257, 1900718.	0.7	1
153	Electron-phonon coupling of epigraphene at millikelvin temperatures measured by quantum transport thermometry. Applied Physics Letters, 2021, 118, 103102.	1.5	1
154	Domain Structure of Thick GaN Layers Grown by Hydride Vapor Phase Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 197-202.	1.0	0
155	Defect Evolution in 4H-SiC Sublimation Epi-Layers Grown on LPE Buffers with Reduced Micropipe Density. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	0
156	Process Induced Extended Defects in SiC Grown via Sublimation. Materials Research Society Symposia Proceedings, 2002, 742, 351.	0.1	0
157	Growth, morphological and structural characterization of silicon carbide epilayers for power electronic devices applications. Crystal Research and Technology, 2005, 40, 964-966.	0.6	0
158	Liquid Phase Epitaxy of Silicon Carbide. , 2007, , 179-201.		0
159	Growth of Silicon Carbide. , 0, , 433-449.		0
160	Structural Evolution of 3C-SiC Grown by Sublimation Epitaxy. , 2010, , .		0
161	Electrical Characterization of p-type 3C-SiC Epilayers Grown on n-type 6H-SiC by means of Sublimation Epitaxy. , 2010, , .		0
162	Terahertz radiation induced edge currents in graphene. , 2011, , .		0

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163	Temperature dependent current transport in Schottky diodes of nano structured ZnO grown on Si by magnetron sputtering. , 2011, , .		0
164	Terahertz radiation induced photocurrents in graphene subjected to an in-plane magnetic field. , 2012, , .		0
165	Breakdown of the quantum Hall effect in graphene. , 2012, , .		0
166	Magnetic quantum ratchet effect in graphene. , 2013, , .		0
167	Fabrication of graphene quantum hall resistance standard in a cryogen-table-top system. , 2016, , .		0
168	Atomic Layer Deposition of AlN on Graphene. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000684.	0.8	0
169	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Meeting Abstracts, 2017, , .	0.0	0
170	Voltage- and Frequency-Dependent Electrical Characteristics and Interface State Density of Ni/ZnO Schottky Diodes. Acta Physica Polonica A, 2022, 141, 99-104.	0.2	0